David J Smith

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

 644
papers
 19,031
citations
 66
h-index
 104
g-index

 685
ext. papers
 20,361
ext. citations
 4.4
avg, IF
 6.64
L-index

#	Paper	IF	Citations
644	The sound of recovery: Coral reef restoration success is detectable in the soundscape. <i>Journal of Applied Ecology</i> , 2022 , 59, 742-756	5.8	3
643	The Role of the Double-Layer Potential in Regularised Stokeslet Models of Self-Propulsion. <i>Fluids</i> , 2021 , 6, 411	1.6	
642	Atomic-Resolution Structure Imaging of Misfit Dislocations at Heterovalent IIIVI/IIIIV Interfaces. <i>ACS Applied Electronic Materials</i> , 2021 , 3, 2573-2579	4	O
641	Impact of Individual Structural Defects in GaAs Solar Cells: A Correlative and In Operando Investigation of Signatures, Structures, and Effects. <i>Advanced Optical Materials</i> , 2021 , 9, 2001487	8.1	3
640	Knocking on the door: policy, agency and path creation in the post-industrial city. <i>European Planning Studies</i> , 2021 , 29, 899-922	3.2	
639	Resolving conservation and development tensions in a small island state: A governance analysis of Curieuse Marine National Park, Seychelles. <i>Marine Policy</i> , 2021 , 127, 103617	3.5	4
638	Heads and Tails: Requirements for Informative and Robust Computational Measures of Sperm Motility 2021 , 135-150		
637	Approaches to Phase Imaging in the Electron Microscope. <i>Microscopy and Microanalysis</i> , 2020 , 26, 1546	5-1 <u>5.</u> \$ 6	
636	A hyperspectral unmixing framework for energy-loss near-edge structure analysis. <i>Ultramicroscopy</i> , 2020 , 218, 113096	3.1	2
635	Effects of growth temperature on electrical properties of GaN/AlN based resonant tunneling diodes with peak current density up to 1.01 MA/cm2. <i>AIP Advances</i> , 2020 , 10, 055307	1.5	5
634	Annealing Effects on the Band Alignment of ALD SiO2 on $(InxGa1 \mbox{12})2O3$ for $x = 0.25 \mbox{13}$. The sum of Solid State Science and Technology, 2020 , 9, 045001	2	
633	Direct Observation of Large Atomic Polar Displacements in Epitaxial Barium Titanate Thin Films. <i>Advanced Materials Interfaces</i> , 2020 , 7, 2000555	4.6	4
632	Prevention of Adrenal Crisis: Cortisol Responses to Major Stress Compared to Stress Dose Hydrocortisone Delivery. <i>Journal of Clinical Endocrinology and Metabolism</i> , 2020 , 105,	5.6	35
631	Changes in band alignment during annealing at 600 $\footnote{l}\f$	2.5	3
630	Investigation of polycrystalline GaxIn1 IkP for potential use as a solar cell absorber with tunable bandgap. <i>Journal of Applied Physics</i> , 2020 , 127, 073102	2.5	2
629	Reverse Leakage Analysis for As-Grown and Regrown Vertical GaN-on-GaN Schottky Barrier Diodes. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 1-1	2.3	19
628	Coral microbiome composition along the northern Red Sea suggests high plasticity of bacterial and specificity of endosymbiotic dinoflagellate communities. <i>Microbiome</i> , 2020 , 8, 8	16.6	26

627	Layered two-dimensional selenides and tellurides grown by molecular beam epitaxy 2020 , 235-269		1
626	Doing more with less: The flagellar end piece enhances the propulsive effectiveness of human spermatozoa. <i>Physical Review Fluids</i> , 2020 , 5,	2.8	7
625	The Making of Innovative Entrepreneurs in Business Schools in a Resource Constrained Environment. <i>Proceedings - Academy of Management</i> , 2020 , 2020, 19277	0.1	
624	Rapid optofluidic detection of biomarkers for traumatic brain injury via surface-enhanced Raman spectroscopy. <i>Nature Biomedical Engineering</i> , 2020 , 4, 610-623	19	49
623	Coral bleaching patterns are the outcome of complex biological and environmental networking. <i>Global Change Biology</i> , 2020 , 26, 68-79	11.4	52
622	Strategies for Analyzing Noncommon-Atom Heterovalent Interfaces: The Case of CdTe-on-InSb. <i>Advanced Materials Interfaces</i> , 2020 , 7, 1901658	4.6	9
621	Structural breakdown in high power GaN-on-GaN p-n diode devices stressed to failure. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020 , 38, 063402	2.9	4
620	Atomic-resolution structure imaging of defects and interfaces in compound semiconductors. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2020 , 66, 100498	3.5	9
619	Dielectric breakdown in epitaxial BaTiO3 thin films. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2020 , 38, 044007	1.3	1
618	Formation of metastable bc8 phase from crystalline Si0.5Ge0.5 by high-pressure torsion. <i>Materials Characterization</i> , 2020 , 169, 110590	3.9	6
617	Passively parallel regularized stokeslets. <i>Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences</i> , 2020 , 378, 20190528	3	4
616	Plasma Enhanced Atomic Layer-etched and Regrown GaN-on-GaN High Power p-n Diodes. <i>Microscopy and Microanalysis</i> , 2020 , 26, 840-842	0.5	
615	Coral microbiome diversity reflects mass coral bleaching susceptibility during the 2016 El Ni B heat wave. <i>Ecology and Evolution</i> , 2019 , 9, 938-956	2.8	28
614	Switching Behavior and Forward Bias Degradation of 700V, 0.2A, EGa2O3Vertical Geometry Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3028-Q3033	2	12
613	Defects at the surface of EGa2O3 produced by Ar plasma exposure. APL Materials, 2019, 7, 061102	5.7	25
612	Damage Recovery and Dopant Diffusion in Si and Sn Ion Implanted EGa2O3. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3133-Q3139	2	20
611	Sharp Quadrature Error Bounds for the Nearest-Neighbor Discretization of the Regularized Stokeslet Boundary Integral Equation. <i>SIAM Journal of Scientific Computing</i> , 2019 , 41, B139-B152	2.6	6
610	Self-assembled Bismuth Selenide (BiSe) quantum dots grown by molecular beam epitaxy. <i>Scientific Reports</i> , 2019 , 9, 3370	4.9	18

609	Strain-dependence of (2) in thin film barium strontium titanate. AIP Advances, 2019, 9, 025312	1.5	3
608	60Co Gamma Ray Damage in Homoepitaxial EGa2O3Schottky Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3041-Q3045	2	10
607	Molecular beam epitaxial growth and structural properties of hetero-crystalline and heterovalent PbTe/CdTe/InSb structures. <i>Journal of Applied Physics</i> , 2019 , 126, 045708	2.5	3
606	Motile curved bacteria are Pareto-optimal. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2019 , 116, 14440-14447	11.5	29
605	Growth Habits of Bismuth Selenide (Bi2Se3) Layers and Nanowires over Stranskill rastanov Indium Arsenide Quantum Dots. <i>Crystal Growth and Design</i> , 2019 , 19, 6989-6993	3.5	2
604	Electron Holography. <i>Springer Handbooks</i> , 2019 , 767-818	1.3	8
603	Quantitative measurement of nanoscale electrostatic potentials and charges using off-axis electron holography: Developments and opportunities. <i>Ultramicroscopy</i> , 2019 , 203, 105-118	3.1	12
602	Epitaxial Oxides on Glass: A Platform for Integrated Oxide Devices. <i>ACS Applied Nano Materials</i> , 2019 , 2, 7713-7718	5.6	4
601	Microstructural Characterization of Defects and Chemical Etching for HgCdSe/ZnTe/Si (211) Heterostructures. <i>Journal of Electronic Materials</i> , 2019 , 48, 571-582	1.9	2
600	Strain relaxation in low-mismatched GaAs/GaAs1-xSbx/GaAs heterostructures. <i>Acta Materialia</i> , 2019 , 162, 103-115	8.4	10
599	Surface structure analysis of Eu Zintl template on Ge(001). Surface Science, 2018, 674, 94-102	1.8	7
598	BIOLOGICAL FLUID MECHANICS UNDER THE MICROSCOPE: A TRIBUTE TO JOHN BLAKE. <i>ANZIAM Journal</i> , 2018 , 59, 416-442	0.5	2
597	Green innovation and the development of sustainable communities: The case of Blueprint Regeneration Trent Basin development. <i>International Journal of Entrepreneurship and Innovation</i> , 2018 , 19, 21-32	1.5	20
596	Nottingham Express Transit: The role of green innovation in the drive for sustainable mobility through improved public transport. <i>International Journal of Entrepreneurship and Innovation</i> , 2018 , 19, 56-68	1.5	2
595	Growth of II-VI/III-V heterovalent quantum structures. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2018 , 36, 02D110	1.3	5
594	Thermal refugia against coral bleaching throughout the northern Red Sea. <i>Global Change Biology</i> , 2018 , 24, e474-e484	11.4	107
593	Crystalline SrZrO3 deposition on Ge (001) by atomic layer deposition for high-k dielectric applications. <i>Journal of Applied Physics</i> , 2018 , 124, 044102	2.5	9
592	Atomic structure of dissociated 60ºdislocations in GaAs/GaAs0.92Sb0.08/GaAs heterostructures. <i>Scripta Materialia</i> , 2018 , 153, 77-80	5.6	4

591	Impact of metastable phases on electrical properties of Si with different doping concentrations after processing by high-pressure torsion. <i>Scripta Materialia</i> , 2018 , 157, 120-123	5.6	11
590	Meshfree and efficient modeling of swimming cells. <i>Physical Review Fluids</i> , 2018 , 3,	2.8	14
589	Effect of SrTiO3 oxygen vacancies on the conductivity of LaTiO3/SrTiO3 heterostructures. <i>Journal of Applied Physics</i> , 2018 , 124, 185303	2.5	14
588	EuO epitaxy by oxygen scavenging on SrTiO3 (001): Effect of SrTiO3 thickness and temperature. <i>Journal of Applied Physics</i> , 2018 , 124, 235301	2.5	6
587	Investigation of defect creation in GaP/Si(0 0 1) epitaxial structures. <i>Journal of Crystal Growth</i> , 2018 , 503, 36-44	1.6	10
586	An EELS signal-from-background separation algorithm for spectral line-scan/image quantification. <i>Ultramicroscopy</i> , 2018 , 195, 25-31	3.1	6
585	Large positive linear magnetoresistance in the two-dimensional t electron gas at the EuO/SrTiO interface. <i>Scientific Reports</i> , 2018 , 8, 7721	4.9	31
584	Nanoparticle transport across model cellular membranes: when do solubility-diffusion models break down?. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 294004	3	10
583	The scientific careers of Robert Sinclair and Nestor Zaluzec - A brief sketch. <i>Ultramicroscopy</i> , 2017 , 176, 2-4	3.1	
582	Zintl layer formation during perovskite atomic layer deposition on Ge (001). <i>Journal of Chemical Physics</i> , 2017 , 146, 052817	3.9	9
581	Structural evolution of dilute magnetic (Sn,Mn)Se films grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2017 , 121, 075301	2.5	5
580	Unraveling Hydrophobic Interactions at the Molecular Scale Using Force Spectroscopy and Molecular Dynamics Simulations. <i>ACS Nano</i> , 2017 , 11, 2586-2597	16.7	28
579	Observation of compound semiconductors and heterovalent interfaces using aberration-corrected scanning transmission electron microscopy. <i>Journal of Materials Research</i> , 2017 , 32, 921-927	2.5	6
578	Surface preparation of freestanding GaN substrates for homoepitaxial GaN growth by rf-plasma MBE. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2017 , 35, 02B10	ე ₫ .3	19
577	High-resolution transmission electron microscopy analysis of bulk nanograined silicon processed by high-pressure torsion. <i>Materials Characterization</i> , 2017 , 129, 163-168	3.9	17
576	Correlation of Etch Pits and Dislocations in As-grown and Thermal Cycle-Annealed HgCdTe(211) Films. <i>Journal of Electronic Materials</i> , 2017 , 46, 5007-5019	1.9	5
575	Can Simple Interaction Models Explain Sequence-Dependent Effects in Peptide Homodimerization?. <i>Journal of Physical Chemistry B</i> , 2017 , 121, 5928-5943	3.4	2
574	Substrate-independent analysis of microcrystalline silicon thin films using UV Raman spectroscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1700204	1.3	4

573	Recent studies of oxide-semiconductor heterostructures using aberration-corrected scanning transmission electron microscopy. <i>Journal of Materials Research</i> , 2017 , 32, 912-920	2.5	7
572	Band offsets of epitaxial cubic boron nitride deposited on polycrystalline diamond via plasma-enhanced chemical vapor deposition. <i>Applied Physics Letters</i> , 2017 , 111, 171604	3.4	11
571	Microscale magnetic compasses. <i>Journal of Applied Physics</i> , 2017 , 122, 094301	2.5	
570	High-resolution transmission electron microscopy analysis of nanograined germanium produced by high-pressure torsion. <i>Materials Characterization</i> , 2017 , 132, 132-138	3.9	16
569	Adaptive capability and path creation in the post-industrial city: the case of Nottingham biotechnology sector. <i>Cambridge Journal of Regions, Economy and Society</i> , 2017 , 10, 491-508	3.3	5
568	Institutions, place leadership and public entrepreneurship: Reinterpreting the economic development of Nottingham. <i>Local Economy</i> , 2017 , 32, 374-392	1.2	17
567	Epitaxial growth of barium titanate thin films on germanium via atomic layer deposition. <i>Journal of Crystal Growth</i> , 2017 , 476, 6-11	1.6	12
566	Integration of ferroelectric BaTiO3 with Ge: The role of a SrTiO3 buffer layer investigated using aberration-corrected STEM. <i>Applied Physics Letters</i> , 2017 , 110, 252901	3.4	5
565	Above 400-K robust perpendicular ferromagnetic phase in a topological insulator. <i>Science Advances</i> , 2017 , 3, e1700307	14.3	96
564	AlGaN/GaN High Electron Mobility Transistor Grown and Fabricated on ZrTi Metallic Alloy Buffer Layers. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, S3078-S3080	2	1
563	Critical issues for homoepitaxial GaN growth by molecular beam epitaxy on hydride vapor-phase epitaxy-grown GaN substrates. <i>Journal of Crystal Growth</i> , 2016 , 456, 121-132	1.6	24
562	Characterization of structural defects in SnSe2 thin films grown by molecular beam epitaxy on GaAs (111)B substrates. <i>Journal of Crystal Growth</i> , 2016 , 453, 58-64	1.6	10
561	Impact of severe plastic deformation on microstructure and hydrogen storage of titanium-iron-manganese intermetallics. <i>Scripta Materialia</i> , 2016 , 124, 108-111	5.6	29
560	Contradictory nature of Co doping in ferroelectric BaTiO3. <i>Physical Review B</i> , 2016 , 94,	3.3	7
559	Direct Mapping of Charge Distribution during Lithiation of Ge Nanowires Using Off-Axis Electron Holography. <i>Nano Letters</i> , 2016 , 16, 3748-53	11.5	31
558	Towards defect-free epitaxial CdTe and MgCdTe layers grown on InSb (001) substrates. <i>Journal of Crystal Growth</i> , 2016 , 439, 99-103	1.6	10
557	Characterization of electrical properties in axial Si-Ge nanowire heterojunctions using off-axis electron holography and atom-probe tomography. <i>Journal of Applied Physics</i> , 2016 , 120, 104301	2.5	9
556	Monolithic integration of perovskites on Ge(001) by atomic layer deposition: a case study with SrHfxTi1-xO3. <i>MRS Communications</i> , 2016 , 6, 125-132	2.7	13

555	Bright-field imaging of compound semiconductors using aberration-corrected scanning transmission electron microscopy. <i>Semiconductor Science and Technology</i> , 2016 , 31, 094002	1.8	7	
554	Structural characterization of niobium oxide thin films grown on SrTiO3 (111) and (La,Sr)(Al,Ta)O3 (111) substrates. <i>Journal of Applied Physics</i> , 2016 , 120, 245302	2.5	10	
553	Evaluation of AlGaN/GaN high electron mobility transistors grown on ZrTi buffer layers with sapphire substrates. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2016 , 34, 051208	1.3	4	
552	Continuous control of spin polarization using a magnetic field. <i>Applied Physics Letters</i> , 2016 , 108, 21240	13.4	1	
551	Evaluation of antimony segregation in InAs/InAs1\(\text{InAs1}\(\text{ISbx}\) type-II superlattices grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2016 , 119, 095702	2.5	35	
550	Investigation of dilute-nitride alloys of GaAsNx (0.01 . <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2016 , 34, 011210	1.3	5	
549	Anti-phase boundaries at the SrTiO3/Si(001) interface studied using aberration-corrected scanning transmission electron microscopy. <i>Applied Physics Letters</i> , 2016 , 108, 091605	3.4	15	
548	Spectral identification scheme for epitaxially grown single-phase niobium dioxide. <i>Journal of Applied Physics</i> , 2016 , 119, 095308	2.5	7	
547	Morphological and microstructural stability of N-polar InAlN thin films grown on free-standing GaN substrates by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016 , 34, 021512	2.9	1	
546	Spectrum and phase mapping across the epitaxial EAl2O3/SrTiO3 interface. <i>Applied Physics Letters</i> , 2016 , 108, 051606	3.4	7	
545	Effect of indium in Al0.65Ga0.35N/Al0.8Ga0.2N MQWs for the development of deep-UV laser structures in the form of graded-index separate confinement heterostructure (GRINSCH). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 1165-1169	1.6	15	
544	Impact of dynamical scattering on quantitative contrast for aberration-corrected transmission electron microscope images. <i>Micron</i> , 2016 , 89, 77-86	2.3	2	
543	Molecular beam epitaxy growth of antimony-based mid-infrared interband cascade photodetectors. <i>Journal of Crystal Growth</i> , 2015 , 425, 364-368	1.6	6	
542	Defect creation in InGaAs/GaAs multiple quantum wells[] Structural properties. <i>Journal of Crystal Growth</i> , 2015 , 425, 43-48	1.6	5	
541	Molecular dynamics simulation study of the association of lidocainium docusate and its derivatives in aqueous solution. <i>Molecular Pharmaceutics</i> , 2015 , 12, 1893-901	5.6	9	
540	Domain structure and perpendicular magnetic anisotropy in CoFe/Pd multilayers using off-axis electron holography. <i>Journal of Magnetism and Magnetic Materials</i> , 2015 , 388, 16-21	2.8	5	
539	MBE growth of sharp interfaces in dilute-nitride quantum wells with improved nitrogen-plasma design. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2015 , 33, 0312	263	8	
538	⊞-antitrypsin variants and the proteinase/antiproteinase imbalance in chronic obstructive pulmonary disease. <i>American Journal of Physiology - Lung Cellular and Molecular Physiology</i> , 2015 , 308 1 179-90	5.8	41	

537	Direct detection and measurement of wall shear stress using a filamentous bio-nanoparticle. <i>Nano Research</i> , 2015 , 8, 3307-3315	10	4
536	Quasi-two-dimensional electron gas at the epitaxial alumina/SrTiO3 interface: Control of oxygen vacancies. <i>Journal of Applied Physics</i> , 2015 , 117, 095303	2.5	34
535	Recovery in dc and rf performance of off-state step-stressed AlGaN/GaN high electron mobility transistors with thermal annealing. <i>Applied Physics Letters</i> , 2015 , 106, 153504	3.4	2
534	Plastic Deformation of BaTiO3 Ceramics by High-pressure Torsion and Changes in Phase Transformations, Optical and Dielectric Properties. <i>Materials Research Letters</i> , 2015 , 3, 216-221	7.4	52
533	Investigation of MBE-grown InAs1 B i alloys and Bi-mediated type-II superlattices by transmission electron microscopy. <i>Journal of Crystal Growth</i> , 2015 , 425, 250-254	1.6	19
532	Glyph-Based Video Visualization for Semen Analysis. <i>IEEE Transactions on Visualization and Computer Graphics</i> , 2015 , 21, 980-93	4	16
531	Investigation of single-layer/multilayer self-assembled InAs quantum dots on GaAs1-xSbx/GaAs composite substrates. <i>Journal of Applied Physics</i> , 2015 , 118, 094303	2.5	4
530	Effect of interfacial oxygen on the microstructure of MBE-grown homoepitaxial N-polar GaN. <i>Journal of Crystal Growth</i> , 2015 , 409, 14-17	1.6	12
529	Determination of Mean Inner Potential and Inelastic Mean Free Path of ZnTe Using Off-Axis Electron Holography and Dynamical Effects Affecting Phase Determination. <i>Microscopy and Microanalysis</i> , 2015 , 21, 1406-1412	0.5	6
528	Charge control in N-polar InAlN high-electron-mobility transistors grown by plasma-assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2015 , 33, 061207	1.3	10
527	Effect of proton irradiation energy on AlGaN/GaN metal-oxide semiconductor high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2015 , 33, 051208	1.3	8
526	Effect of spacer layer thickness on structural and optical properties of multi-stack InAs/GaAsSb quantum dots. <i>Applied Physics Letters</i> , 2015 , 107, 173109	3.4	8
525	Quasi-two-dimensional electron gas at the interface of FAl2O3/SrTiO3 heterostructures grown by atomic layer deposition. <i>Journal of Applied Physics</i> , 2015 , 118, 115303	2.5	22
524	Simultaneous Enhancement of Electrical Conductivity and Thermopower of Billelby Multifunctionality of Native Defects. <i>Advanced Materials</i> , 2015 , 27, 3681-6	24	79
523	An indirect method of studying band alignments in nBn photodetectors using off-axis electron holography. <i>Applied Physics Letters</i> , 2015 , 107, 122109	3.4	4
522	Polymerase Chain Reaction on a Viral Nanoparticle. ACS Synthetic Biology, 2015, 4, 1316-25	5.7	3
521	Formation of metastable phases in magnesium tanium system by high-pressure torsion and their hydrogen storage performance. <i>Acta Materialia</i> , 2015 , 99, 150-156	8.4	52
520	Measurement of mean inner potential and inelastic mean free path of ZnO nanowires and nanosheet. <i>Materials Research Express</i> , 2015 , 2, 105003	1.7	3

519	Atomic layer deposition of crystalline SrHfO3 directly on Ge (001) for high-k dielectric applications. Journal of Applied Physics, 2015 , 117, 054101	2.5	39
518	Carrier density modulation in a germanium heterostructure by ferroelectric switching. <i>Nature Communications</i> , 2015 , 6, 6067	17.4	64
517	Chapter 1:Characterization of Nanomaterials Using Transmission Electron Microscopy. <i>RSC Nanoscience and Nanotechnology</i> , 2015 , 1-29		12
516	Atomic-scale chemical imaging and quantification of metallic alloy structures by energy-dispersive X-ray spectroscopy. <i>Scientific Reports</i> , 2014 , 4, 3945	4.9	57
515	Molecular beam epitaxy using bismuth as a constituent in InAs and a surfactant in InAs/InAsSb superlattices. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2014 , 32, 02C120	1.3	23
514	Effect of proton irradiation on AlGaN/GaN high electron mobility transistor off-state drain breakdown voltage. <i>Applied Physics Letters</i> , 2014 , 104, 082106	3.4	15
513	Enhancement of AlGaN/GaN high electron mobility transistors off-state drain breakdown voltage via backside proton irradiation. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2014 , 32, 021203	1.3	6
512	Characterization of a-plane GaN templates grown by HVPE and high efficiency deep UV emitting AlGaN/AlN MQWs grown by MBE on such templates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 585-589		3
511	Nanostructure P roperty Control in AlPSi3/Si(100) Semiconductors Using Direct Molecular Assembly: Theory Meets Experiment at the Atomic Level. <i>Chemistry of Materials</i> , 2014 , 26, 4092-4101	9.6	6
510	Optimization of In2Se3/Si(111) Heteroepitaxy To Enable Bi2Se3/In2Se3 Bilayer Growth. <i>Crystal Growth and Design</i> , 2014 , 14, 4617-4623	3.5	5
509	Fabrication of nanograined silicon by high-pressure torsion. <i>Journal of Materials Science</i> , 2014 , 49, 6565	-645569	26
508	Left-right organizer flow dynamics: how much cilia activity reliably yields laterality?. <i>Developmental Cell</i> , 2014 , 29, 716-28	10.2	63
507	Improvisation and Entrepreneurial Bricolage versus Rationalisation: A case-based analysis of contrasting responses to economic instability in the UK brass musical instruments industry. <i>Journal of General Management</i> , 2014 , 40, 53-78	1.3	16
506	Linking, leveraging and learning: sectoral systems of innovation and technological catch-up in China's commercial aerospace industry. <i>Global Business and Economics Review</i> , 2014 , 16, 349	0.5	3
505	Atomic Scale Studies of Structure and Bonding in A1PSi3 Alloys Grown Lattice-matched on Si(001). <i>Microscopy and Microanalysis</i> , 2014 , 20, 524-525	0.5	1
504	Using structural disorder to enhance the magnetism and spin-polarization in FexSi1 Athin films for spintronics. <i>Materials Research Express</i> , 2014 , 1, 026102	1.7	10
503	Improving the Spatial Resolution of Atomic-Scale EDS Mapping for Chemical Imaging and Quantification of Metallic Alloy Structures. <i>Microscopy and Microanalysis</i> , 2014 , 20, 130-131	0.5	
502	A Chemical Route to Monolithic Integration of Crystalline Oxides on Semiconductors. <i>Advanced Materials Interfaces</i> , 2014 , 1, 1400081	4.6	38

501	Epitaxial growth: Phenomenological model of defect creation 2014 ,		1
500	Band alignment of a HfO2-VO2-HfO2 confined well structure on silicon. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2014 , 32, 011203	1.3	5
499	Epitaxy of polar semiconductor Co3O4 (110): Growth, structure, and characterization. <i>Journal of Applied Physics</i> , 2014 , 115, 243708	2.5	19
498	Atomic and electronic structure of the ferroelectric BaTiO3/Ge(001) interface. <i>Applied Physics Letters</i> , 2014 , 104, 242908	3.4	40
497	Microstructure of Ti/Al/Ni/Au ohmic contacts for N-polar GaN/AlGaN high electron mobility transistor devices. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2014 , 32, 011201	1.3	5
496	Determination of polarization-fields across polytype interfaces in InAs nanopillars. <i>Advanced Materials</i> , 2014 , 26, 1052-7	24	26
495	Microscopic Investigation of Mono-layer/Multi-layer self-assembled InAs QDs on GaAs1-xSbx/GaAs Composite Substrates for Photovoltaic Solar Cells. <i>Microscopy and Microanalysis</i> , 2014 , 20, 554-555	0.5	
494	Ultrathin-barrier AlN/GaN heterostructures grown by rf plasma-assisted molecular beam epitaxy on freestanding GaN substrates. <i>Journal of Crystal Growth</i> , 2013 , 380, 14-17	1.6	19
493	Structure and morphology of polar and semi-polar pyramidal surfaces coating wurtzite ZnO micro-wires. <i>Journal of Materials Science</i> , 2013 , 48, 3857-3862	4.3	10
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(2011-2012)

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365 364 363	Growth of III-nitride quantum dots and their applications to blue-green LEDs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2560-2565 An atomistic branching mechanism for carbon nanotubes: sulfur as the triggering agent. <i>Angewandte Chemie - International Edition</i> , 2008 , 47, 2948-53 Structural characterization of non-polar (1 1 2 0) and semi-polar (1 1 2 6) GaN films grown on r-plane sapphire. <i>Journal of Crystal Growth</i> , 2008 , 310, 2981-2986	1.6 16.4 1.6	256919
365 364 363 362	Growth of III-nitride quantum dots and their applications to blue-green LEDs. <i>Physica Status Solidi</i> (A) Applications and Materials Science, 2008, 205, 2560-2565 An atomistic branching mechanism for carbon nanotubes: sulfur as the triggering agent. <i>Angewandte Chemie - International Edition</i> , 2008, 47, 2948-53 Structural characterization of non-polar (1 1 2 0) and semi-polar (1 1 2 6) GaN films grown on r-plane sapphire. <i>Journal of Crystal Growth</i> , 2008, 310, 2981-2986 Progress and perspectives for atomic-resolution electron microscopy. <i>Ultramicroscopy</i> , 2008, 108, 159-69. Heterodoped nanotubes: theory, synthesis, and characterization of phosphorus-nitrogen doped	1.6 16.4 1.6 66.1	25691917
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(2006-2007)

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179	Spin-dependent tunneling in discontinuous CoBiO2 magnetic tunnel junctions. <i>Applied Physics Letters</i> , 1998 , 73, 535-537	3.4	38
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177	Effect of ammonia flow rate on impurity incorporation and material properties of Si-doped GaN epitaxial films grown by reactive molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1998 , 84, 6680-668	5 ^{2.5}	14
176	Microstructural study of Mg-doped p-type GaN: Correlation between high-resolution electron microscopy and Raman spectroscopy. <i>Journal of Applied Physics</i> , 1997 , 82, 6008-6011	2.5	15
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174	Growth and structural characterization of highly oriented sputter-deposited (111), (110), and (100) Co/Cu superlattices. <i>Applied Physics Letters</i> , 1997 , 71, 1480-1482	3.4	9
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170	Growth of AlN and GaN on 6HBiC(0001) using a helium supersonic beam seeded with ammonia. <i>Applied Physics Letters</i> , 1997 , 71, 1365-1367	3.4	18
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163	Reflectivity difference spectroscopy study of thin film ZnSe grown on GaAs by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1997 , 175-176, 328-333	1.6	5
162	Chemical Synthesis of Metastable Germanium Tarbon Alloys Grown Heteroepitaxially on (100) Si. <i>Chemistry of Materials</i> , 1996 , 8, 2491-2498	9.6	10
161	HREM study of 45º[100]quasiperiodic grain boundary in aluminum. <i>Scripta Materialia</i> , 1996 , 35, 327-331	5.6	3
160	An investigation of grain boundaries in submicrometer-grained Al-Mg solid solution alloys using high-resolution electron microscopy. <i>Journal of Materials Research</i> , 1996 , 11, 1880-1890	2.5	291

159	Structural properties of GaN films grown on sapphire by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1996 , 68, 1141-1143	3.4	50
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157	Growth of high quality CdTe on Si substrates by molecular beam epitaxy. <i>Journal of Electronic Materials</i> , 1996 , 25, 1402-1405	1.9	29
156	Evolution of grain boundary structure in submicrometer-grained Al-Mg alloy. <i>Materials Characterization</i> , 1996 , 37, 285-294	3.9	28
155	Heteroepitaxial CdTe(111) grown by MBE on nominally flat and misoriented Si(001) substrates: characterization by electron microscopy and optical methods. <i>Journal of Crystal Growth</i> , 1996 , 159, 58-6	3.6	12
154	Optical characterization of ZnMnSSe quaternary alloys for visible light emitting devices. <i>Journal of Crystal Growth</i> , 1996 , 159, 50-53	1.6	4
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152	Low temperature inorganic chemical vapor deposition of heteroepitaxial GaN. <i>Applied Physics Letters</i> , 1996 , 69, 203-205	3.4	27
151	The effect of carbon on strain relaxation and phase formation in the Ti/Si1MJGexCy/Si contact system. <i>Applied Physics Letters</i> , 1996 , 69, 64-66	3.4	29
150	Strain measurements of SiGeC heteroepitaxial layers on Si(001) using ion beam analysis. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1996 , 14, 441-446	2.9	10
149	Synthesis and characterization of heteroepitaxial diamond-structured Ge1IICx (x=1.5I.0%) alloys using chemical vapor deposition. <i>Applied Physics Letters</i> , 1996 , 68, 2407-2409	3.4	43
148	Measurement of lattice-fringe vectors from digital HREM images: experimental precision. <i>Ultramicroscopy</i> , 1995 , 57, 409-422	3.1	41
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144	Characterization of structural defects in wurtzite GaN grown on 6H SiC using plasma-enhanced molecular beam epitaxy. <i>Applied Physics Letters</i> , 1995 , 67, 1830-1832	3.4	77
143	Growth and characterization of pseudomorphic single crystal zinc blende MnS. <i>Applied Physics Letters</i> , 1995 , 67, 2690-2692	3.4	57
142	Microstructure of heteroepitaxial CdTe grown on misoriented Si(001) substrates. <i>Applied Physics Letters</i> , 1995 , 67, 1591-1593	3.4	54

141	Dynamic processes at InP(110) surfaces studied by UHV reflection electron microscopy. <i>Surface Science</i> , 1995 , 340, 141-152	1.8	4
140	Novel Synthetic Routes to Carbon Nitride. <i>Chemistry of Materials</i> , 1995 , 7, 1422-1426	9.6	54
139	Formation of threading defects in GaN wurtzite films grown on nonisomorphic substrates. <i>Applied Physics Letters</i> , 1995 , 67, 2063-2065	3.4	138
138	Growth of heteroepitaxial Si1\(\mathbb{N}\)GexCy alloys on silicon using novel deposition chemistry. <i>Applied Physics Letters</i> , 1995 , 67, 1247-1249	3.4	23
137	Chemical vapor deposition of heteroepitaxial Si1MJGexCy films on (100)Si substrates. <i>Applied Physics Letters</i> , 1994 , 65, 2559-2561	3.4	78
136	Novel chemical routes to silicon-germanium-carbon materials. <i>Applied Physics Letters</i> , 1994 , 65, 2960-29	96,24	31
135	Direct observation of potential distribution across Si/Si p-n junctions using off-axis electron holography. <i>Applied Physics Letters</i> , 1994 , 65, 2603-2605	3.4	114
134	Characterization of WCx/B4C multilayers sputtered in reactive argon/methane atmospheres. <i>Thin Solid Films</i> , 1994 , 239, 57-70	2.2	8
133	Microstructural characterization of Co/Cu multilayers. <i>Journal of Magnetism and Magnetic Materials</i> , 1994 , 129, 415-422	2.8	17
132	High resolution imaging of magnetic multilayers. <i>Scripta Metallurgica Et Materialia</i> , 1994 , 30, 689-694		6
131	Dependence of giant magnetoresistance on grain size in Co/Cu multilayers. <i>Physical Review B</i> , 1994 , 50, 4232-4235	3.3	32
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129	Reflection electron microscopy studies of GaP(110) surfaces in UHV-TEM. <i>Surface Science</i> , 1993 , 287-288, 1062-1066	1.8	2
128	Dependence of giant magnetoresistance on Cu-layer thickness in Co/Cu multilayers: A simple dilution effect. <i>Physical Review B</i> , 1993 , 47, 9136-9139	3.3	42
127	Characterization of WC x /B 4 C multilayers sputtered in argon/methane atmospheres 1993 , 1742, 354		1
126	Comparative study of supported catalyst particles by electron microscopy methods. <i>Ultramicroscopy</i> , 1993 , 52, 282-288	3.1	13
125	Progress towards quantitative high-resolution electron microscopy. <i>Ultramicroscopy</i> , 1993 , 52, 591-601	3.1	15
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106	Electron-beam-induced surface reactions in Pd/PdO films. <i>Surface Science</i> , 1991 , 250, 90-98	1.8	6

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10	Ultra-high-resolution electron microscopy of amorphous materials at 120 kV. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1981 , 43, 907-923		27
9	The observation of amorphous materials at high voltage and high resolution. <i>Journal of Microscopy</i> , 1980 , 119, 19-28	1.9	7
8	Investigations of the structure of amorphous and partially crystalline metallic alloys by high resolution electron microscopy. <i>Journal of Microscopy</i> , 1980 , 119, 63-72	1.9	24
7	Observations on the structure of amorphous arsenic by high resolution electron microscopy. <i>Journal of Microscopy</i> , 1980 , 119, 29-37	1.9	4
6	Atomic resolution with a 600-kV electron microscope. <i>Nature</i> , 1979 , 281, 49-51	50.4	43
5	High resolution imaging of amorphous materials. <i>Nature</i> , 1979 , 281, 54-55	50.4	22
4	Direct observation of the structure of a metallic alloy glass. <i>Nature</i> , 1979 , 281, 465-467	50.4	42
3	Observations of silicon carbide by high resolution transmission electron microscopy. <i>Journal of Microscopy</i> , 1978 , 114, 1-18	1.9	37
2	Aperture contrast in thick amorphous specimens using scanning transmission electron microscopy. <i>Ultramicroscopy</i> , 1975 , 1, 127-36	3.1	21
1	Motile curved bacteria are Pareto-optimal		1